

~~Excluded~~ ~~Patents~~

4. (original) The apparatus according to claim 1, further comprising a rotation apparatus for rotating the fixture.
5. (original) The apparatus according to claim 1, further comprising a circulation apparatus for circulating the etchant solution.
6. (original) The apparatus according to claim 1, further comprising a temperature adjustment apparatus for adjusting the temperature of the etchant solution.
7. (original) The apparatus according to claim 1, wherein the etchant solution is maintained at a temperature in the range of about 40°C to 50°C.
8. (original) The apparatus according to claim 1, wherein the semiconductor material includes indium phosphide.
9. (original) The apparatus according to claim 1, wherein the thinned semiconductor wafers are incorporated into devices selected from the group consisting of microwave circuits, millimeter wave circuits, and combinations thereof.
10. (original) The apparatus according to claim 1, wherein the thinned semiconductor wafers have a final thickness in the range of about 25 to 250 µm.
11. <sup>presented</sup> ~~(previously-amended)~~ A method for simultaneously thinning the backside surfaces of a plurality of wafers comprised of a semiconductor material, comprising:
  - providing a fixture having a plurality of horizontally orientated receptacles for receiving the plurality of semiconductor wafers;
  - loading the plurality of semiconductor wafers into the plurality of receptacles;
  - providing an etchant solution capable of isotropically removing a layer of semiconductor material from the backside surface of the plurality of semiconductor wafers, wherein the etchant solution is comprised of a mixture of acetic acid, hydrogen

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